

A large, stylized white arc graphic that starts from the left, curves upwards and to the right, and then curves back down towards the left, resembling a partial circle or a protective shield.

IGBT

TRENCHSTOP™ IGBT3 Chip
SIGC54T65R3E

Data Sheet

Industrial Power Control

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SIGC54T65R3E

TRENCHSTOP™ IGBT3 Chip

Features:

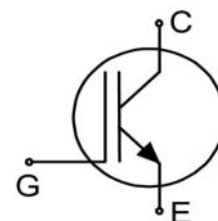
- 650V trench & field stop technology
- Low V_{CEsat}
- Low turn-off losses
- Short tail current
- Positive temperature coefficient
- Easy paralleling

Recommended for:

- Power modules

Applications:

- Drives



| Chip Type | V_{CE} | I_{Cn} | Die Size | Package |
|--------------|----------|----------|-----------------|--------------|
| SIGC54T65R3E | 650V | 100A | 5.97mm x 8.97mm | Sawn on foil |

Mechanical Parameters

| | | | |
|--|----------------------------------|---|-----------------|
| Die size | | 5.97 x 8.97 | mm ² |
| Emitter pad size | | See chip drawing | |
| Gate pad size | | 1.615 x 0.817 | |
| Area total | | 53.55 | |
| Silicon thickness | | 70 | µm |
| Wafer size | | 200 | mm |
| Maximum possible chips per wafer | | 486 | |
| Passivation frontside | | Photoimide | |
| Pad metal | | 3200nm AlSiCu | |
| Backside metal | | Ni Ag – system To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process | |
| Die bond | | Electrically conductive epoxy glue and soft solder | |
| Wire bond | | Al, ≤500µm | |
| Reject ink dot size | | Ø 0.65mm; max. 1.2mm | |
| Storage environment (<6 months) | for original and sealed MBB bags | Ambient atmosphere air, temperature 17°C – 25°C | |
| | for open MBB bags | Acc. IEC 62258-3; Section 9.4 Storage Environment. | |

Maximum Ratings

In general, from reliability and lifetime point of view, the lower the operation junction temperature and/or the applied voltage, the greater the expected lifetime of any semiconductor device.

| Parameter | Symbol | Value | Unit |
|---|--------------------|------------------|--------------------|
| Collector-emitter voltage, $T_{vj}=25^{\circ}\text{C}$ | V_{CE} | 650 | V |
| DC collector current, limited by $T_{vj\text{ max}}^1$ | I_C | - | A |
| Pulsed collector current, t_p limited by $T_{vj\text{ max}}^2$ | $I_{C,puls}$ | 300 | A |
| Gate-emitter voltage | V_{GE} | ± 20 | V |
| Junction temperature | T_{vj} | $-40 \dots +175$ | $^{\circ}\text{C}$ |
| Operating junction temperature | $T_{vj\text{ op}}$ | $-40 \dots +150$ | $^{\circ}\text{C}$ |
| Short circuit data $^{1/2/3}$ $V_{GE}=15\text{V}$, $V_{CC}=360\text{V}$, $T_{vj}=150^{\circ}\text{C}$ | t_{sc} | 6 | μs |

Static Characteristics (tested on wafer), $T_{vj}=25^{\circ}\text{C}$

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|---------------|---|-------|------|------|---------------|
| | | | min. | typ. | max. | |
| Collector-emitter breakdown voltage | $V_{(BR)CES}$ | $V_{GE}=0\text{V}$, $I_C=4\text{mA}$ | 650 | - | - | V |
| Collector-emitter saturation voltage | V_{CEsat} | $V_{GE}=15\text{V}$, $I_C=100\text{A}$ | 0.93 | 1.45 | 1.77 | |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C=1.6\text{mA}$, $V_{GE}=V_{CE}$ | 5.1 | 5.8 | 6.4 | |
| Zero gate voltage collector current | I_{CES} | $V_{CE}=650\text{V}$, $V_{GE}=0\text{V}$ | - | - | 5.4 | μA |
| Gate-emitter leakage current | I_{GES} | $V_{CE}=0\text{V}$, $V_{GE}=20\text{V}$ | - | - | 600 | nA |
| Integrated gate resistor | r_G | | - | 2 | - | Ω |

Electrical Characteristics ²

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|-------------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| Collector-emitter saturation voltage | V_{CEsat} | $V_{GE}=15\text{V}$, $I_C=100\text{A}$ $T_{vj}=150^{\circ}\text{C}$ | - | 1.7 | - | V |
| Input capacitance | C_{ies} | $V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=1\text{MHz}$ $T_{vj}=25^{\circ}\text{C}$ | - | 6160 | - | pF |
| Reverse transfer capacitance | C_{res} | | - | 183 | - | |

¹ Depending on thermal properties of assembly.

² Not subject to production test - verified by design/characterization.

³ Allowed number of short circuits: <1000; time between short circuits: >1s.



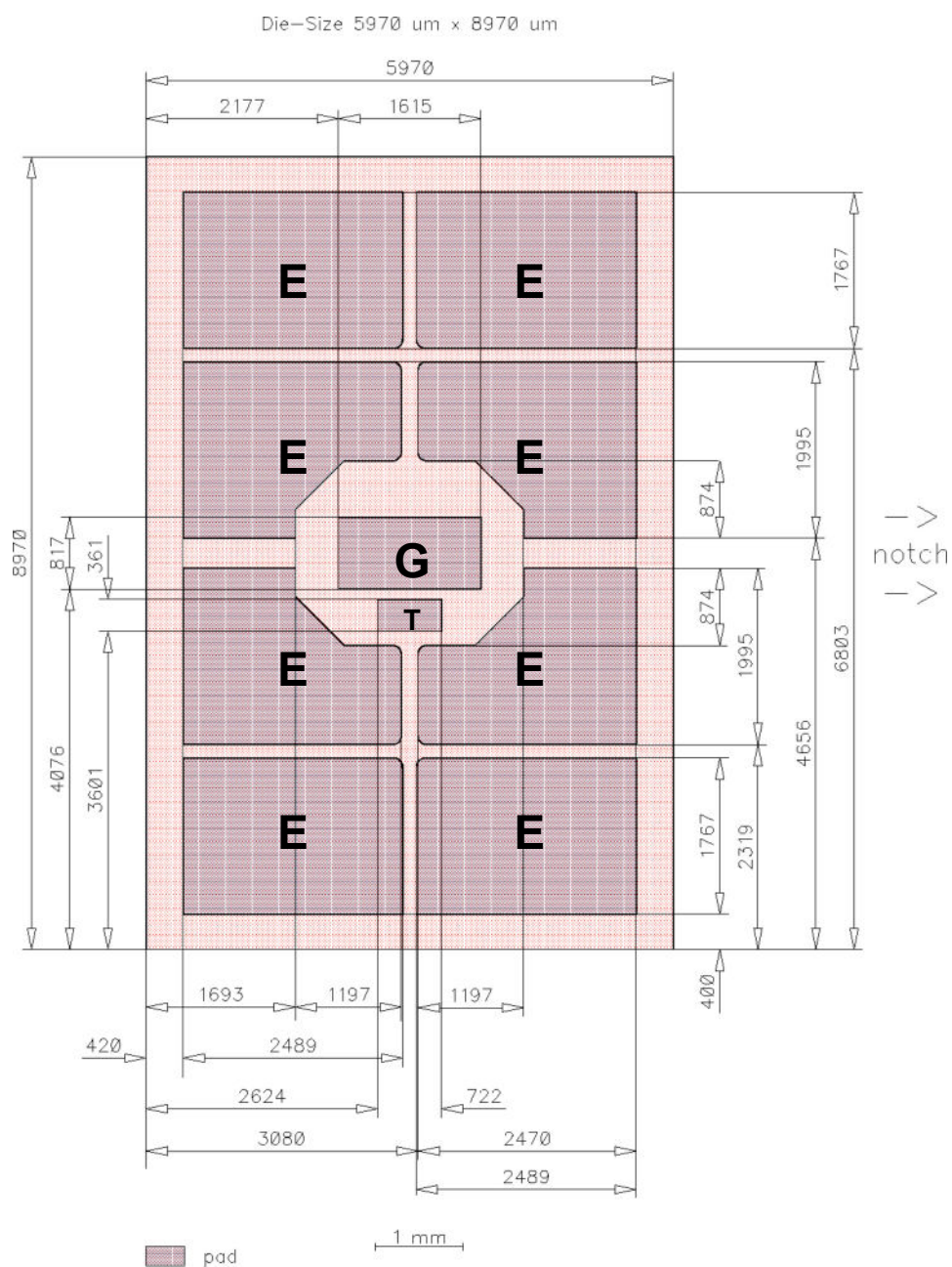
SIGC54T65R3E

Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

| | | |
|---------------------|-------------------|----------|
| Application example | F3L100R07W2E3_B11 | Rev. 2.1 |
|---------------------|-------------------|----------|

Chip Drawing



E = Emitter

G = Gate

T = Test pad do not contact



SIGC54T65R3E

Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

| Revision | Subjects (major changes since last revision) | Date |
|----------|--|------------|
| 2.0 | Final data sheet | 04.11.2016 |
| | | |
| | | |

Relevant Application Notes

| | |
|--|--|
| | |
|--|--|

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